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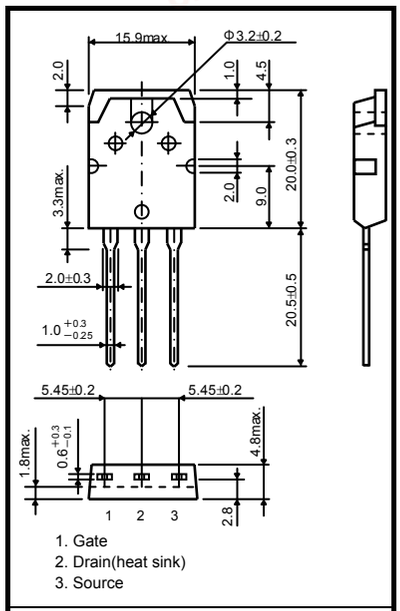
TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (DTMOS)

TK40J60T

Switching Regulator Applications

- Low drain-source ON resistance: $R_{DS\ (ON)}$ = 0.068 Ω (typ.)
- High forward transfer admittance: $|Y_{fs}|$ = 25 S (typ.)
- Low leakage current: I_{DSS} = 100 μA (V_{DS} = 600 V)
- Enhancement-mode: V_{th} = 3.0~5.0 V (V_{DS} = 10 V, I_D = 1 mA)

Unit: mm



JEDEC	—
JEITA	SC-65
TOSHIBA	2-16C1B

Weight : 4.6 g (typ.)

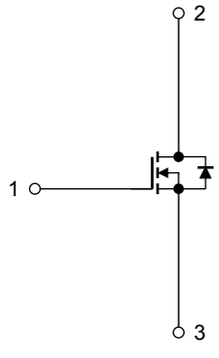
Absolute Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit
Drain-source voltage		V_{DSS}	600	V
Gate-source voltage		V_{GSS}	±30	V
Drain current	DC (Note 1)	I_D	40	A
	Pulse (t = 1 ms) (Note 1)	I_{DP}	80	
Drain power dissipation (Tc = 25°C)		P_D	400	W
Single pulse avalanche energy (Note 2)		E_{AS}	576	mJ
Avalanche current (Note 3)		I_{AR}	40	A
Repetitive avalanche energy		E_{AR}	40	mJ
Channel temperature		T_{ch}	150	°C
Storage temperature range		T_{stg}	-55~150	°C

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook (“Handling Precautions”/”Derating Concept and Methods”) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case	$R_{th\ (ch-c)}$	0.313	°C/W
Thermal resistance, channel to ambient	$R_{th\ (ch-a)}$	50	°C/W



Note 1: Please use devices on conditions that the channel temperature is below 150°C.

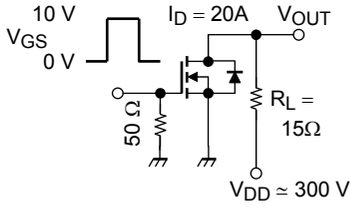
Note 2: V_{DD} = 90 V, T_{ch} = 25 °C (initial), L = 0.63 mH, R_G = 25 Ω, I_{AR} = 40 A

Note 3: Repetitive rating: pulse width limited by maximum channel temperature

This transistor is an electrostatic sensitive device. Please handle with caution.

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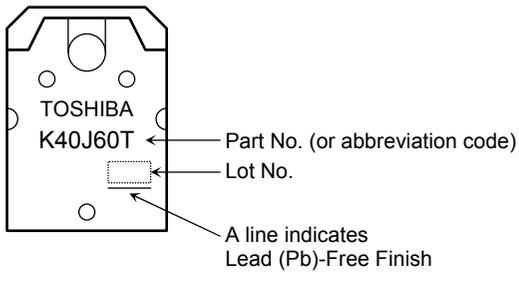
Electrical Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		I_{GSS}	V_{GS} = ±30 V, V_{DS} = 0 V	—	—	±1	μA
Drain cut-off current		I_{DSS}	V_{DS} = 600 V, V_{GS} = 0 V	—	—	100	μA
Drain-source breakdown voltage		$V_{(BR)\ DSS}$	I_D = 10 mA, V_{GS} = 0 V	600	—	—	V
Gate threshold voltage		V_{th}	V_{DS} = 10 V, I_D = 1 mA	3.0	—	5.0	V
Drain-source ON resistance		$R_{DS\ (ON)}$	V_{GS} = 10 V, I_D = 20 A	—	0.068	0.08	Ω
Forward transfer admittance		$\|Y_{fs}\|$	V_{DS} = 20 V, I_D = 20 A	6	25	—	S
Input capacitance		C_{iss}	V_{DS} = 10 V, V_{GS} = 0 V, f = 1 MHz	—	3900	—	pF
Reverse transfer capacitance		C_{rss}		—	280	—	
Output capacitance		C_{oss}		—	9200	—	
Switching time	Rise time	t_r	 Duty ≦ 1%, t_w = 10 μs	—	60	—	ns
	Turn-on time	t_{on}		—	120	—	
	Fall time	t_f		—	15	—	
	Turn-off time	t_{off}		—	200	—	
Total gate charge		Q_g	V_{DD} ≃ 400 V, V_{GS} = 10 V, I_D = 40 A	—	67	—	nC
Gate-source charge		Q_{gs}		—	45	—	
Gate-drain charge		Q_{gd}		—	22	—	

Source-Drain Ratings and Characteristics (Ta = 25°C)

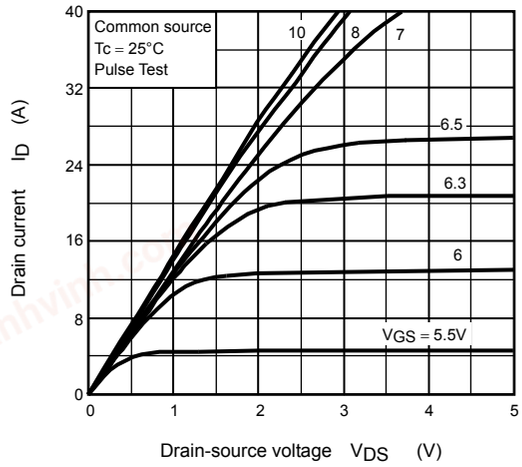
Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Continuous drain reverse current (Note 1)	I_{DR}	—	—	—	40	A
Pulse drain reverse current (Note 1)	I_{DRP}	—	—	—	80	A
Forward voltage (diode)	V_{DSF}	I_{DR} = 40 A, V_{GS} = 0 V	—	—	-1.7	V
Reverse recovery time	t_{rr}	I_{DR} = 40 A, V_{GS} = 0 V, dI_{DR}/dt = 100 A/μs	—	550	—	ns
Reverse recovery charge	Q_{rr}		—	14	—	μC

Marking

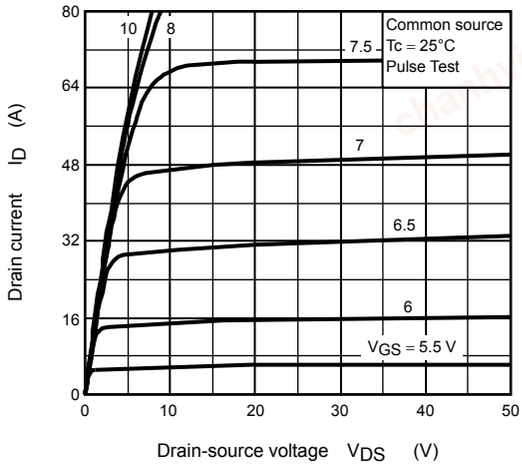


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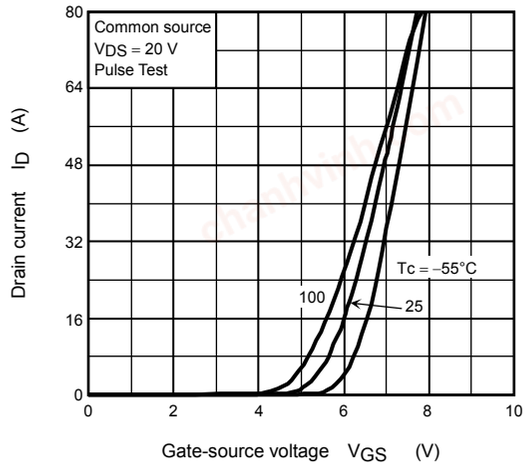
$I_D - V_{DS}$



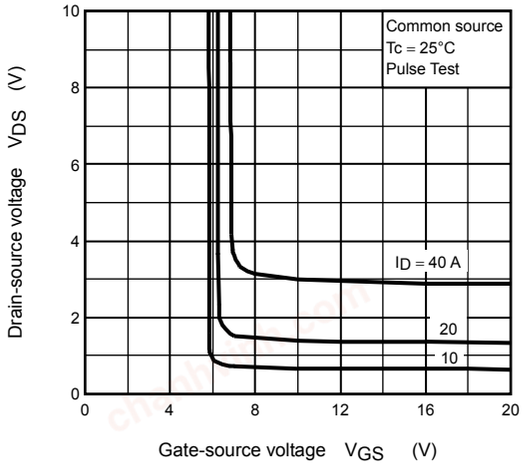
$I_D - V_{DS}$



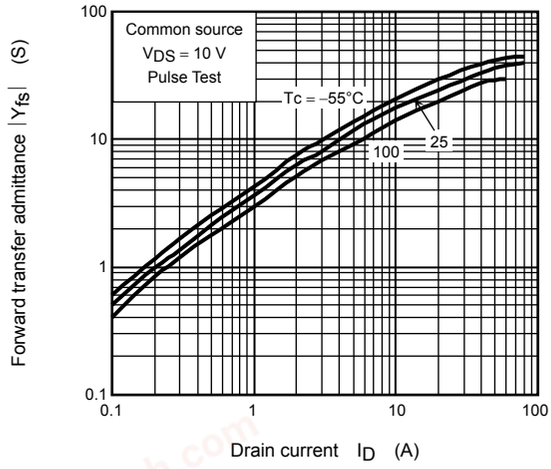
$I_D - V_{GS}$



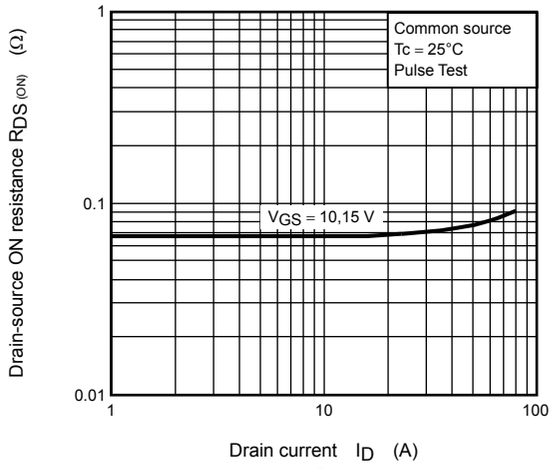
$V_{DS} - V_{GS}$



$|Y_{fs}| - I_D$

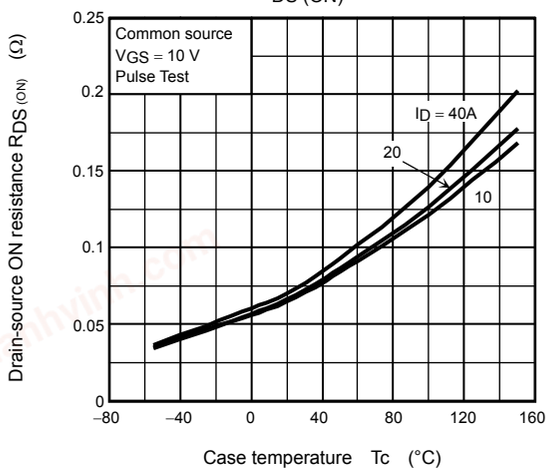


$R_{DS\ (ON)} - I_D$

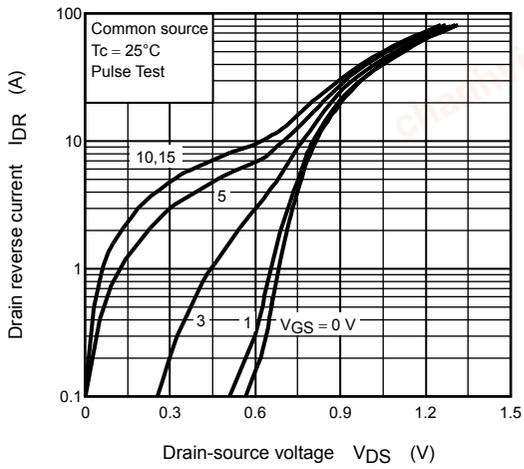


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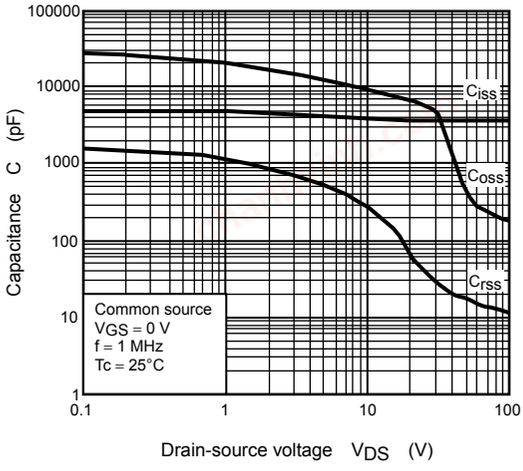
$R_{DS\ (ON)}$ – Tc



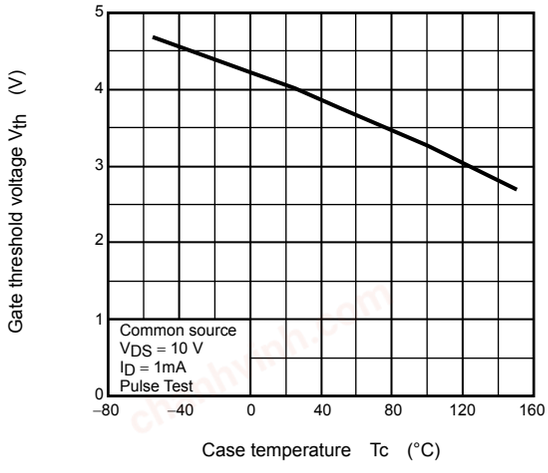
I_{DR} – V_{DS}



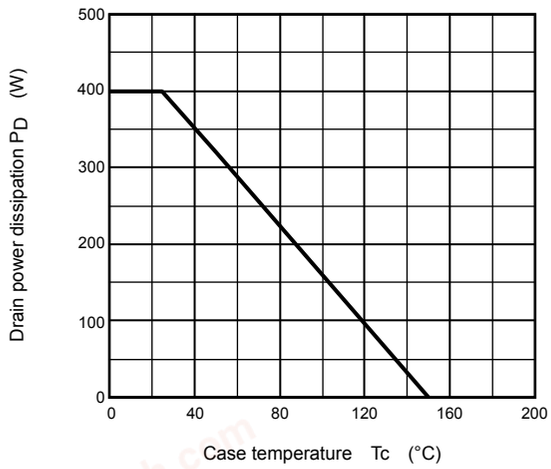
Capacitance – V_{DS}



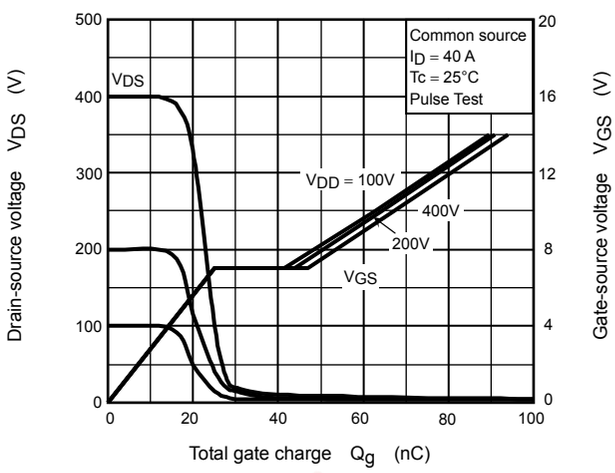
V_{th} – Tc



P_D – Tc

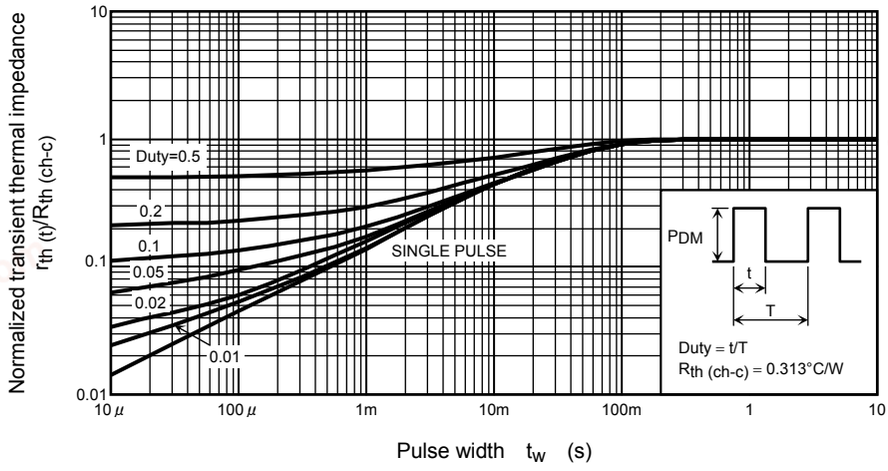


Dynamic input / output characteristics

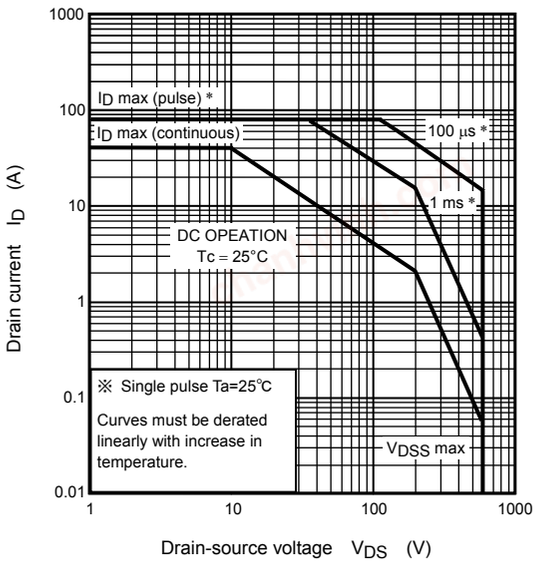


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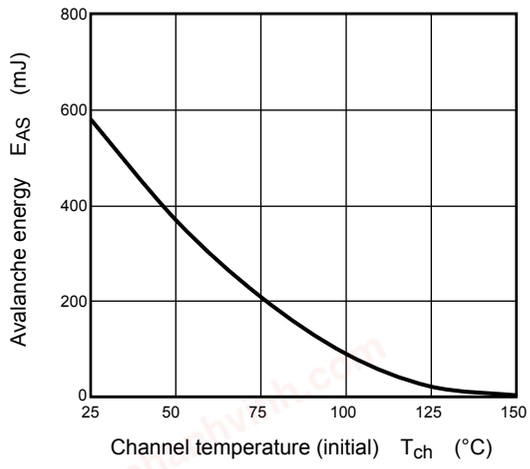
$r_{th} - t_w$

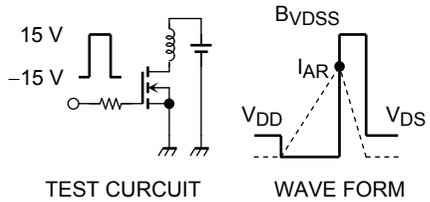


SAFE OPERATING AREA



$E_{AS} - T_{ch}$





TEST CURCUIT WAVE FORM

$R_G = 25\ \Omega$
$V_{DD} = 90$ V, L = 0.63 mH

$$E_{AS} = \frac{1}{2} \cdot L \cdot I^2 \cdot \left(\frac{B_{VDSS}}{B_{VDSS} - V_{DD}} \right)$$

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